Differences of Structural and Electronic Properties in Ba_{1-x}K_xBiO₃ (*x*=0, 0.04, and 0.4)

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Electronic structures calculated based upon the extended Huckel tight-binding method for $Ba_{1-x}K_xBiO_3$ with x = 0, 0.04, and 0.4 are reported. It is noticed that the commensurate ordering of Bi^{3+} and Bi^{5+} is responsible for the insulating and semiconducting behavior in $BaBiO_3$ and $Ba_{0.96}K_{0.04}BiO_4$. The band gaps of 3.2 eV and 1.4 eV for the former and the latter compounds, respectively, are consistent with the experimental results. Doping in Bi 6s-block band up to x = 0.4 causes the collapse of the ordering of Bi^{3+} and Bi^{5+} , thereby resulting in the superconductivity in the $Ba_{0.6}K_{0.4}BiO_3$ compound. Strikingly, the character of oxygen contributes to the conducting mechanism than that of the bismuth. This is quite different from the cuprate superconductors in which the character of copper dominates that of oxygen.

Introduction

The recent growth of interest in the copper-free superconductors is due to, in part, no further progress of raising the superconducting transition temperature during a past decade and limitations to apply for many electronic and electric devices in the copper-oxide high- T_c superconductors. In addition, the non-cuprate materials are attractive to many scientists since these materials may provide clues to understands the roles of the phonon-electron interactions in the microscopic pairing mechanism of high- T_c superconductors. As a consequence of the effort to discover the non-cuprate superconductors, the quaternary and ternary intermetallic compounds, such as LnLi₂B₂C ($T_c = 16.6$ K),¹ YPd₅B₃C_{0.3} $(T_c = 23 \text{ K})^2$ and lanthanum nickel boro-nitride $(T_c = 13 \text{ K})^3$ were synthesized. Before the success of preparations of those three compounds, alkali metal doped fullerides, A₃C₆₀ $(A_3 = Na_2Cs, K_3, Rb_3, K_2Rb, Rb_2K, and Rb_2Cs)$ were found to be superconducting with the T_c up to 31 K when $A_3 =$ Rb₂Cs.⁴⁻¹¹ The T_c's of these non-cuprate compounds are similar to or lower than that of Ba1-xKxBiO3 which was synthesized just after the discovery of high- T_c copper-oxide superconductors.12

Ba_{1-x}K_xBiO₃ is originated from the insulating BaBiO₃ compound. When Scholder *et al.* first synthesized BaBiO₃¹³ whose structure was closely related to that of perovskite, the substantial interest in this compound was made on the oxidation state of Bi. Upon the formal charges of Ba²⁺ and O²⁻, the oxidation state of Bi is +4 which indicates that the electronic structure of Bi is 6s¹ at the ground state. However, Scholder et. al. assumed that the oxidation state of Bi was not Bi⁴⁺ but the mixture of Bi³⁺ and Bi⁵⁺ which were known to exist in many bismuth oxides. A similar opinion was proposed by Nakamura *et al.*¹⁴ that the oxidation states of Bi in the compound were either Ba₂(Bi³⁺Bi⁵⁺)O₆ or the "filled Bi⁴⁺ band". On the other hand, de Hair and Blasse resolved the oxidation state of Bi by using infrared spectroscopy and concluded that Bi favored Bi⁴⁺ in the BaBiO₃ compound.¹⁵ Cox and Sleight refined the structure of the compound with the use of neutron diffraction powder data.¹⁶ Analyzing the inequivalent Bi-O bond distances found in BaBiO₃, they concluded that the compound consisted of Bi³⁺ and Bi⁵⁺ in equal amount rather than Bi⁴⁺, and the Bi³⁺ and Bi⁵⁺ cations took on an ordered arrangement. The insulating property found in BaBiO₃ was supposed to be the result of a commensurate charge-density-wave (CDW) involving the ordering of Bi³⁺ and Bi⁵⁺ into distinct crystallographic sites.

Superconductivity was found in the perovskite-type $BaPb_{1-x}Bi_xO_3$ by Sleight *et al.*¹⁷ which exhibited superconducting transition temperature varing from 0.45 K when x = 0 to 13 K when x = 0.25. The substitution of Bi with Pb results in the collapse of commensurate ordering made by Bi^{3+} and Bi^{5+} and consequently the compound becomes metallic (superconducting). When *x* became larger than 0.25 it showed semiconducting property. Likewise $BaBiO_3$, the semiconducting behavior was thought to be the reason why Bi^{3+} and Bi^{5+} are ordered as the amount of Bi increases. In spite of having the low T_c , the discovery of superconductivity in the substituted $BaBiO_3$ compound encourged to investigate the analogues of this system.

The success to synthesize the Ba_{1-x}K_xBiO₃ system was motivated by the idea that an appropriate doping method might suppress the semiconducting property associated with the commensurate CDW found in BaBiO3 and create a metallic (and superconducting) compound. The oxidation state of Bi in Ba_{1-x}K_xBiO₃ is 4 + x. As x increases the number of holes in the Bi 6s band increase. Superconducting state can be achieved when the balanced ordering of Bi3+ and Bi^{5+} is broken as x increases in this compound. Schneemever et al. reported¹⁸ the growth and structural characterization of single crystals of $Ba_{1-x}K_xBiO_3$ when x = 0, 0.04, and 0.4. The compound becomes superconducting when x = 0.4 with the T_c of 30.5 K. So far no systematic study on this compound with various x values has been made. It is important, therefore, to investigate the differences of structural and electronic properties between insulating (*i.e.*, x = 0), semiconducting (*i.e.*, x = 0.04), and superconducting (*i.e.*, x = 0.4) compounds. In this paper, electronic structures calculated based upon the extended Huckel tight-binding method¹⁹ for Ba_{1-x}K_xBiO₃ with x = 0, 0.04, and 0.4 are reported.

Structure. The structure of the BaBiO₃ at room temperature is monoclinic which is made up of distorted perovskite units. In this compound, two different BiO₆ octahedra are connected alternatively by edge-sharing mode along the crystallographic a- and c-directions, as shown in Figure 1(a). One octahedron is tilted from the vertical c-axis and the next one is tilted in opposite direction to construct a zigzag structure with the angle of 159.9° (see Figure 1(a)). The Bi-O distances in one octahedron are 2.15 Å and 2.13 Å for axial and equatorial, respectively and those in the next octahedron are 2.25 Å and 2.27 Å, respectively. It was speculated that the short and long Bi-O distances indicate the charge disproportionation occurred in the way that $2Bi^{4+} \rightarrow Bi^{3+} + Bi^{5+}$, which results in the insulating property in this compound.

The structure of Ba_{0.96}K_{0.04}BiO₃ is similar to that of the pristine BaBiO₃ in that two different octahedra are connected alternatively along the a- and c-directions. Any octahedron is not tilted from the vertical c-axis in this compound, however, so that the axis line to connect the octahedra along the c-direction is straight. The Bi-O bond distances in an octahedron are 2.22 Å and 2.11 Å for axial and equatorial, respectively, and 2.11 Å and 2.23 Å, respectively in the next octahedron. Two short and four long Bi-O bonds construct the first octahedron, while two long and four short ones are the components of the next. In Ba0.96K0.04BiO3 compound, therefore, two environmentally different Bi are still alternatively ordered as in the case of BaBiO₃. This ordering is consistent with the fact that the compound exhibited semiconducting property. Because of the existence of two structurally different octahedra, the unit cells of BaBiO₃ and Ba_{0.96}K_{0.04}BiO₃ consist of four octahedra as shown in Figure 1. Further substitution for Ba by K in Ba_{1-x}K_xBiO₃ results in the cubic structure in which each unit cell is made up of one octahedron when x = 0.4 (*i.e.*, all octahedra are identical). The Bi-O distance in the BiO₆ octahedron in this compound is 2.1435 Å for both axial and equatorial bonds.

Results and Discussion

The Bi 6s-block bands of BaBiO₃, Ba_{0.96}K_{0.04}BiO₃, and

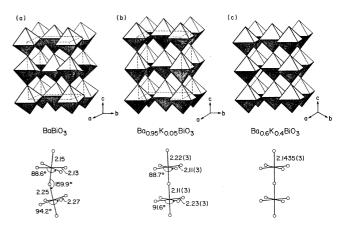


Figure 1. Structural representation of $Ba_{1-x}K_xBiO_3$ for (a) x=0, (b) x=0.04, and (c) x=0.4. Dotted lines refer to the unit cell. Lower portions represent the bond distances and angles. [ref. 18]

Ba_{0.6}K_{0.4}BiO₃ are shown in Figures 2a, 2b, and 2c. Four Bi 6s bands occur in BaBiO₃ and Ba_{0.96}K_{0.04}BiO₃ since four octahedra construct the unit cells of these two compounds. Similarly, only one Bi 6s band is shown in cubic Ba_{0.6}K_{0.4}BiO₃. It was found from the resistivity experiments that BaBiO₃ and Ba_{0.96}K_{0.04}BiO₃ exhibit insulating and semiconducting property, respectively. Our calculation is consistent with the experimental results that the band gap of BaBiO₃ and Ba_{0.96}K_{0.04}BiO₃ are 3.2 eV and 1.4 eV, respectively (see Figures 2a and 2b). Differently from the two compounds, Ba_{0.4}K_{0.4}BiO₃ shows metallic property as shown in Figure 2c (*i.e.*, the Bi 6s-block band is cut by the Fermi energy). Since the oxidation state of Bi is +4.4 in this compound, the Bi 6s band is less than half-filled. It is clear from Figure 2c that the band is almost equally dispersive along the a-, b-, and c-directions which means the compound is a three-dimensional metal. In the band structure of BaBiO₃, however, the valence and conduction bands are strongly dispersive along the crystallographic a-direction but it is almost flat along the b- and c-directions. This is reasonable because an BiO₆ octahedron is symmetrically connected to the neighboring one by edge-sharing mode along each direction in Ba_{0.6}K_{0.4}BiO₃, while different BiO₆ octahedra are ordered alternatively in BaBiO3 and Ba0.96K0.04BiO3 compounds. The amount of orbital interactions depend upon the symmetry of bonding orbitals. Highly symmetric

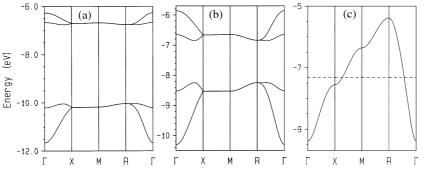


Figure 2. The Bi 6s-bolck bands of $Ba_{1-x}K_xBiO_3$ for (a) x=0, (b) x=0.04, and (c) x=0.4. The dashed line refers to Fermi energy.

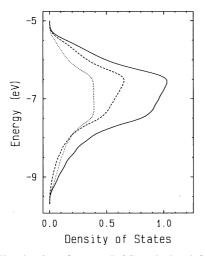
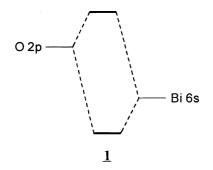


Figure 3. The density of states (DOS) calculated for $Ba_{0.6}K_{0.4}$ -BiO₃. The solid, dashed, and dotted lines refer to the projected DOS of total, Bi 6s, and O 2p contributions, respectively.

Ba_{0.4}K_{0.6}BiO₃ compound, therefore, show larger orbital interactions in every direction, thereby illustrating a strongly dispersive band. The width of the Bi 6s-block band is about 4 eV, which is close to the value obtained from the ab initio calculation. Metallic property found in this compound arises from the fact that the environments of all Bi are identical and each Bi contains same amount of holes upon the substitution for Ba with K. The shape of this band is similar to the highest lying d-block band (*i.e.*, x^2-y^2 band of Cu which is cut by the Fermi energy) found in the high- T_c copper-oxide superconductors.²⁰

The x²-y² band in the cuprate superconductors consists of largely Cu d-orbitals and small amount of O p-orbitals. Holes generated in the hole superconductors (*i.e.*, high- T_c copper-oxide superconductors) are, therefore, mainly contributed by copper d-characters. The highest lying Bi 6sblock band of BaBiO₃ which is cut by the Fermi energy is composed of Bi 6s and O 2p characters. Strikingly the O 2p contribution to the partially filled band in Ba_{0.6}K_{0.4}BiO₃ is larger than the Bi 6s contribution, as shown in the projected density of states (see Figure 3). Consequently, the character of oxygen contributes to the conducting mechanism more than that of the bismuth in $Ba_{0.6}K_{0.4}BiO_3$ compound which is different from the copper-oxide superconductors. It is understandable when the Bi 6s-block band in superconducting Ba_{0.6}K_{0.4}BiO₃ is antibonding level between O 2p and Bi 6s since the energy level of O 2p is higher than that of Bi 6s, as



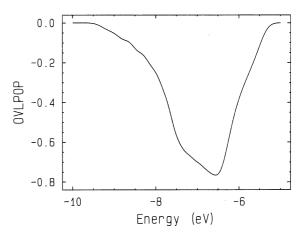


Figure 4. The atomic overlap population calculated for $Ba_{0.6}K_{0.4}$ -BiO₃.

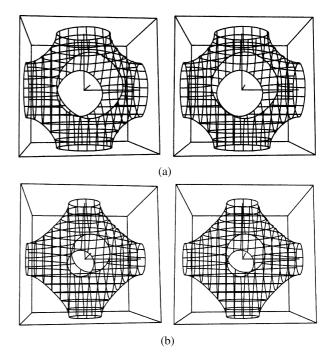


Figure 5. Fermi surfaces calculated for $Ba_{0.6}K_{0.4}BiO_3$ when (a) the Bi 6s-block band is half-filled, and (b) the Bi 6s-block band is less than half-filled.

illustrated in **1**. The atomic orbital overlap population (see Figure 4) shows that the Bi 6s-block band has antibonding property between Bi 6s and O 2p, as expected.

The three dimensional Fermi surfaces associated with the band of $Ba_{0.6}K_{0.4}BiO_3$ for half-filled and less than half-filled (*i.e.*, real) situations are shown in Figures 5a and 5b. Upon the oxidation states of Ba^{2+} . K⁺, and O²⁻, that of Bi in the $Ba_{0.6}K_{0.4}BiO_3$ compound becomes $Bi^{4.4+}$ which means the Bi 6s band is less than half-filled in this case. The Bi 6s-block band is fully occupied when it is Bi^{3+} , but completely empty when Bi^{5+} . As mentioned earlier, the oxidation state of Bi in the pristine $BaBiO_3$ is not Bi^{4+} but Bi^{3+} and Bi^{5+} coexist by charge disproportionation. The Bi 6s-block band is half-filled, therefore, when Bi^{3+} and Bi^{5+} coexist with same

amount to make an average oxidation state of Bi^{4+} . As shown in Figure 5, the Fermi surface for the less than halffilled shows nesting-like behavior but that for the half-filled no nesting. Fermi surface nesting is susceptible to cause the metal-insulator transition *via* CDW. In general, the CDW and superconductivity competes with one another, with the CDW tending to suppress superconductivity and vice versa.²¹ A metal-superconductor transition is stronger in the Ba_{0.6}K_{0.4}BiO₃ compound although very weak Fermi surface nesting is observed. It means that the driving force is not enough to show a metal-insulator transition since the gap is not formed over the entire Fermi surface.

Conclusions

The commensurate ordering of Bi^{3+} and Bi^{5+} is responsible for the insulating and semiconducting behavior in $BaBiO_3$ and $Ba_{0.96}K_{0.04}BiO_4$. The band gaps of 3.2 eV and 1.4 eV for the former and the latter compounds, respectively, are consistent with the experimental results. Doping in Bi 6s-block band causes the collapse of the ordering of Bi^{3+} and Bi^{5+} , thereby resulting in the superconductivity in the $Ba_{0.6}K_{0.4}$ -BiO₃ compound. Strikingly, the character of oxygen contributes to the conducting mechanism than that of the bismuth. This is quite different from the cuprate superconductors in which the character of copper dominates that of oxygen.

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